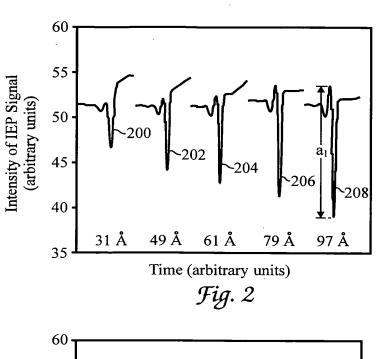


Fig. 1c



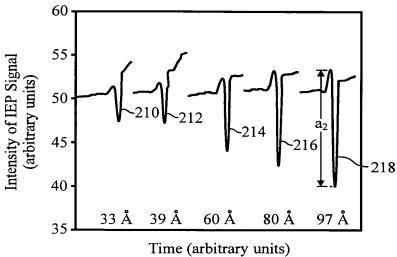


Fig. 3

Gate Oxide Thickness (Å)

(Doped Polysilicon)

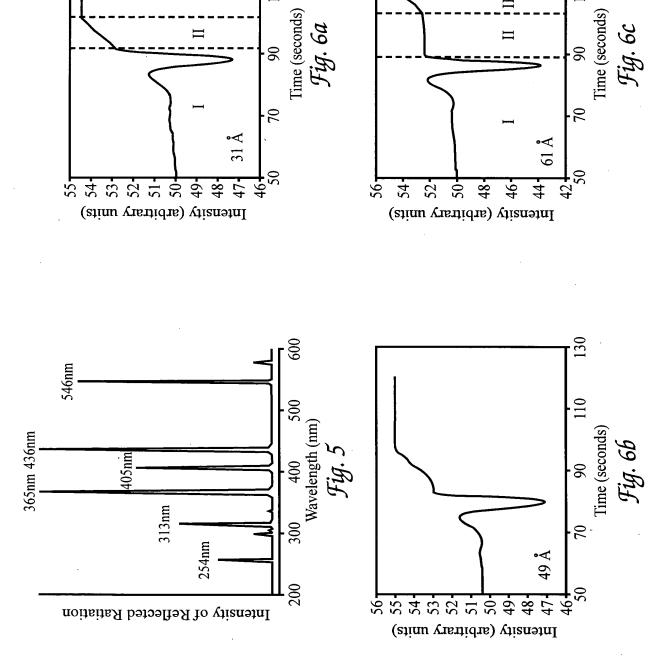
220

(Undoped Polysilicon)

222

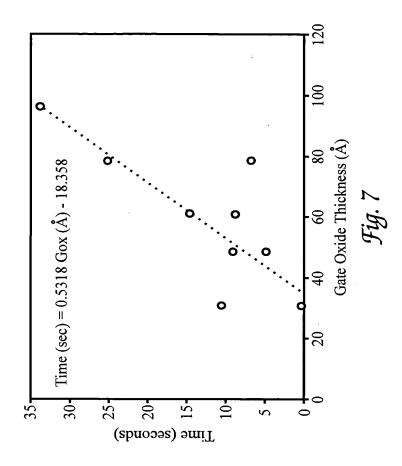
(Undoped Polysilicon)

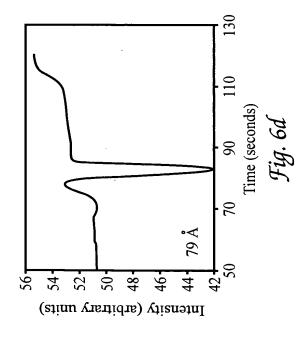
Fig. 4

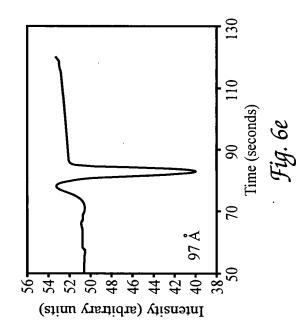


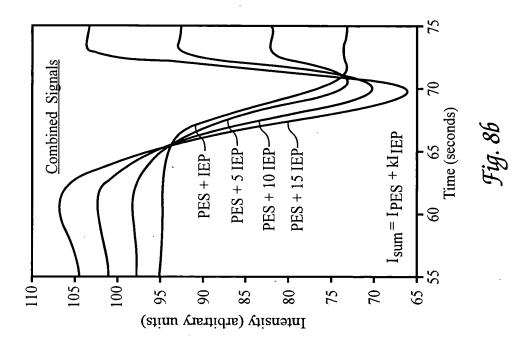
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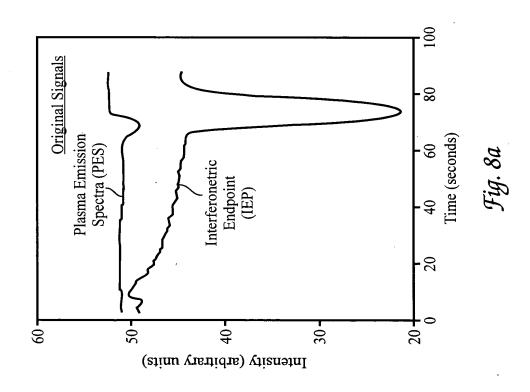
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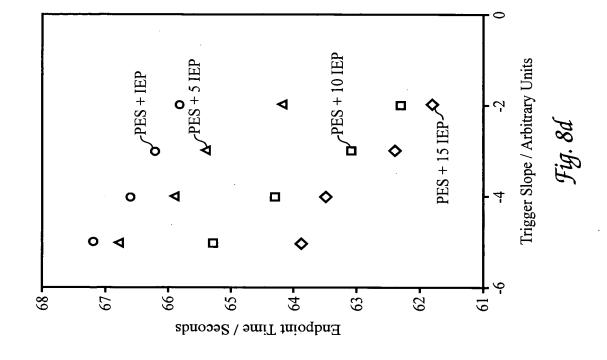












Derivative of Intensity / Arbitrary Units

Derivative of Intensity / Arbitrary Units

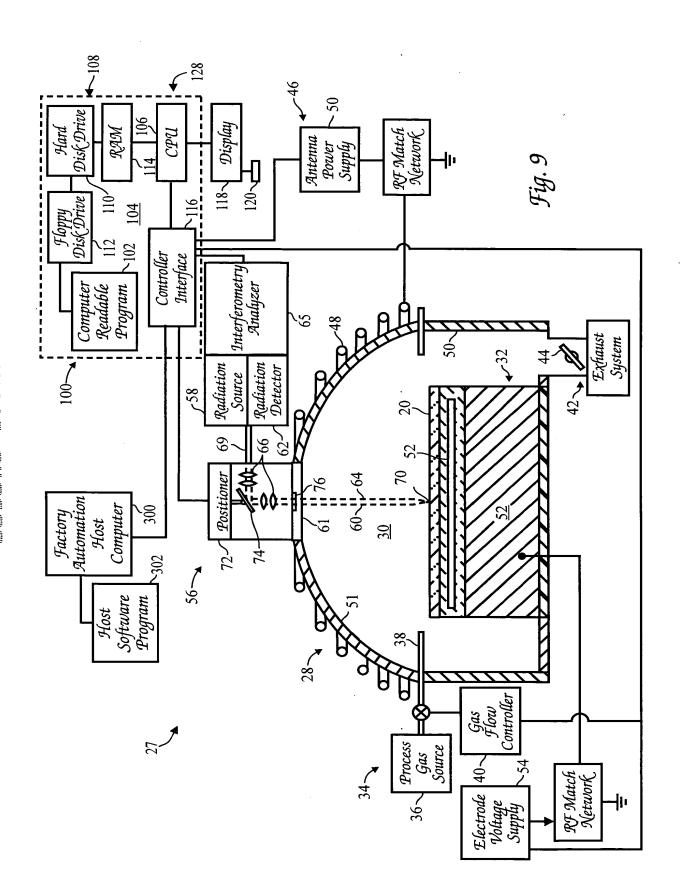
PES + 15 IEP

PES + 16 IEP

PES + 16 IEP

Time / seconds

Fig. 8c



C

